

2SB1645

Silicon PNP triple diffusion planar type Darlington

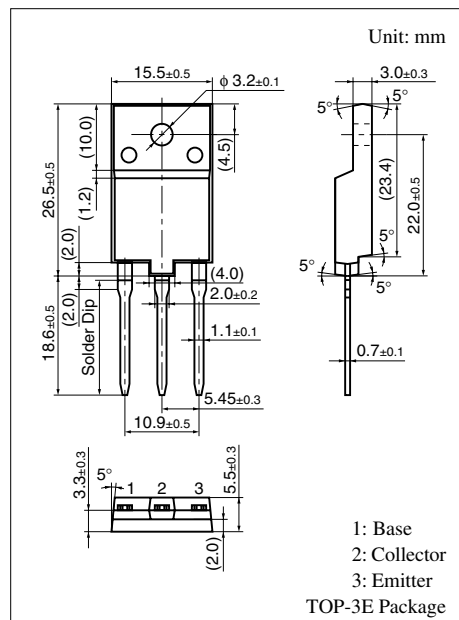
For power amplification

■ Features

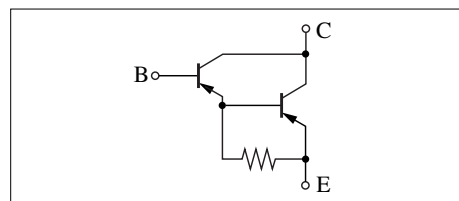
- Satisfactory forward current transfer ratio h_{FE} characteristics
- Wide area of safe operation (ASO)
- Optimum for the output stage of a HiFi audio amplifier

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-160	V
Collector to emitter voltage	V_{CEO}	-160	V
Emitter to base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-15	A
Collector current	I_C	-8	A
Collector power dissipation	$T_C = 25^\circ\text{C}$ $T_a = 25^\circ\text{C}$	P_C	W
		100 3	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Internal Connection



■ Electrical Characteristics $T_C = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -160\text{ V}, I_E = 0$			-100	μA
	I_{CEO}	$V_{CB} = -160\text{ V}, I_E = 0$			-100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$			-100	μA
Collector to emitter voltage	V_{CEO}	$I_C = -10\text{ mA}, I_B = 0$	-160			V
Forward current transfer ratio	h_{FE1}	$V_{CE} = -5\text{ V}, I_C = -1\text{ A}$	500			
	h_{FE2}^*	$V_{CE} = -5\text{ V}, I_C = -7\text{ A}$	3 500		15 000	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -7\text{ A}, I_B = -7\text{ mA}$			-3	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -7\text{ A}, I_B = -7\text{ mA}$			-3	V
Transition frequency	f_T	$V_{CE} = -10\text{ V}, I_C = -0.5\text{ A}, f = 1\text{ MHz}$		20		MHz
Turn-on time	t_{on}	$I_C = 7\text{ A}, I_{B1} = -7\text{ mA}, I_{B2} = 7\text{ mA}$		1.0		μs
Storage time	t_{stg}	$V_{CC} = -50\text{ V}$		1.5		μs
Fall time	t_f			1.2		μs

Note) *: Rank classification

Rank	P	Q
h_{FE2}	5 000 to 15 000	3 500 to 10 000

